Dual-bit, dual-supply voltage level translator/transceiver; 3-state

Rev. 7 — 20 February 2018

Product data sheet

1 General description

The 74AVCH2T45 is a dual bit, dual supply transceiver that enables bidirectional level translation. It features two data input-output ports (nA and nB), a direction control input (DIR) and dual supply pins ($V_{CC(A)}$ and $V_{CC(B)}$). Both $V_{CC(A)}$ and $V_{CC(B)}$ can be supplied at any voltage between 0.8 V and 3.6 V making the device suitable for translating between any of the low voltage nodes (0.8 V, 1.2 V, 1.5 V, 1.8 V, 2.5 V and 3.3 V). Pins nA and DIR are referenced to $V_{CC(A)}$ and pins nB are referenced to $V_{CC(B)}$. A HIGH on DIR allows transmission from nA to nB and a LOW on DIR allows transmission from nB to nA.

The device is fully specified for partial power-down applications using I_{OFF} . The I_{OFF} circuitry disables the output, preventing any damaging backflow current through the device when it is powered down. In suspend mode when either $V_{CC(A)}$ or $V_{CC(B)}$ are at GND level, both A and B are in the high-impedance OFF-state.

The 74AVCH2T45 has active bus hold circuitry which is provided to hold unused or floating data inputs at a valid logic level. This feature eliminates the need for external pull-up or pull-down resistors.

2 Features and benefits

- Wide supply voltage range:
 - V_{CC(A)}: 0.8 V to 3.6 V
 - V_{CC(B)}: 0.8 V to 3.6 V
- High noise immunity
- Complies with JEDEC standards:
 - JESD8-12 (0.8 V to 1.3 V)
 - JESD8-11 (0.9 V to 1.65 V)
 - JESD8-7 (1.2 V to 1.95 V)
 - JESD8-5 (1.8 V to 2.7 V)
 - JESD8-B (2.7 V to 3.6 V)
- ESD protection:
 - HBM JESD22-A114F Class 3B exceeds 8000 V
 - MM JESD22-A115-A exceeds 200 V
 - CDM JESD22-C101C exceeds 1000 V
- · Maximum data rates:
 - 500 Mbps (1.8 V to 3.3 V translation)
 - 320 Mbps (< 1.8 V to 3.3 V translation)
 - 320 Mbps (translate to 2.5 V or 1.8 V)
 - 280 Mbps (translate to 1.5 V)
 - 240 Mbps (translate to 1.2 V)
- Suspend mode
- Bus hold on data inputs

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- · Latch-up performance exceeds 100 mA per JESD 78 Class II
- Inputs accept voltages up to 3.6 V
- Low noise overshoot and undershoot < 10 % of V_{CC}
- I_{OFF} circuitry provides partial Power-down mode operation
- Multiple package options
- Specified from -40 °C to +85 °C and -40 °C to +125 °C

3 Ordering information

Table 1. Ordering i	nformation			
Type number	Package			
	Temperature range	Name	Description	Version
74AVCH2T45DC	-40 °C to +125 °C	VSSOP8	plastic very thin shrink small outline package; 8 leads; body width 2.3 mm	SOT765-1
74AVCH2T45GT	-40 °C to +125 °C	XSON8	plastic extremely thin small outline package; no leads; 8 terminals; body 1 × 1.95 × 0.5 mm	SOT833-1
74AVCH2T45GF	-40 °C to +125 °C	XSON8	extremely thin small outline package; no leads; 8 terminals; body 1.35 × 1 × 0.5 mm	SOT1089
74AVCH2T45GN	-40 °C to +125 °C	XSON8	extremely thin small outline package; no leads; 8 terminals; body 1.2 × 1.0 × 0.35 mm	SOT1116
74AVCH2T45GS	-40 °C to +125 °C	XSON8	extremely thin small outline package; no leads; 8 terminals; body 1.35 × 1.0 × 0.35 mm	SOT1203

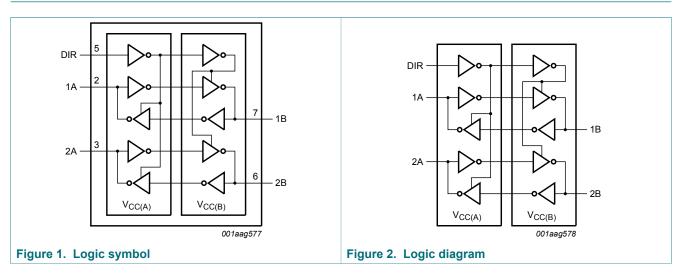
4 Marking

Type number	Marking code ^[1]				
74AVCH2T45DC	K45				
74AVCH2T45GT	K45				
74AVCH2T45GF	К5				
74AVCH2T45GN	К5				
74AVCH2T45GS	К5				

[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

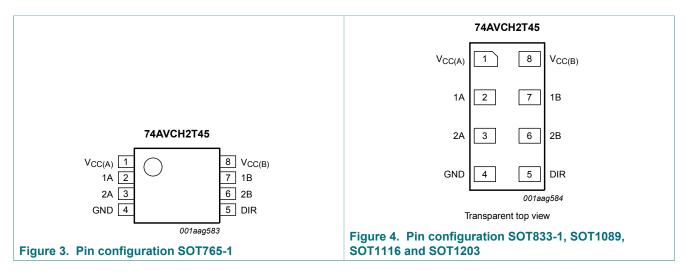
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5 Functional diagram



6 **Pinning information**

6.1 Pinning



6.2 Pin description

Table 3. Pin descri	Table 3. Pin description						
Symbol	Pin	Description					
V _{CC(A)}	1	supply voltage port A and DIR					
1A	2	data input or output					
2A	3	data input or output					
GND	4	ground (0 V)					
DIR	5	direction control					
2B	6	data input or output					
1B	7	data input or output					
V _{CC(B)}	8	supply voltage port B					

Functional description 7

Table 4. Function table

H = HIGH voltage level; L = LOW voltage level; X = don't care; Z = high-impedance OFF-state.

Supply voltage	Input	Input/output ^[1]			
V _{CC(A)} , V _{CC(B)}	DIR ^[2]	nA	nB		
0.8 V to 3.6 V	L	nA = nB	input		
0.8 V to 3.6 V	Н	input	nB = nA		
GND ^[3]	X	Z	Z		

The input circuit of the data I/O is always active.
 The DIR input circuit is referenced to V_{CC(A)}.
 If at least one of V_{CC(A)} or V_{CC(B)} is at GND level, the device goes into suspend mode.

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Limiting values 8

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{CC(A)}	supply voltage A			-0.5	+4.6	V
V _{CC(B)}	supply voltage B			-0.5	+4.6	V
I _{IK}	input clamping current	V _I < 0 V		-50	-	mA
VI	input voltage		[1]	-0.5	+4.6	V
I _{OK}	output clamping current	V _O < 0 V		-50	-	mA
Vo	output voltage	Active mode	[1] [2] [3]	-0.5	V _{CCO} + 0.5	V
		Suspend or 3-state mode	[1]	-0.5	+4.6	V
I _O	output current	$V_{O} = 0 V$ to V_{CCO}		-	±50	mA
I _{CC}	supply current	I _{CC(A)} or I _{CC(B)}		-	100	mA
I _{GND}	ground current			-100	-	mA
T _{stg}	storage temperature			-65	+150	°C
P _{tot}	total power dissipation	T _{amb} = -40 °C to +125 °C	[4]	-	250	mW

[1] The minimum input voltage rating and output voltage ratings may be exceeded if the input and output current ratings are observed.

 V_{CCO} is the supply voltage associated with the output port. [2]

[3] V_{CCO} + 0.5 V should not exceed 4.6 V. [4] For VSSOP8 package: above 110 °C the value of P_{tot} derates linearly with 8 mW/K.

For XSON8 packages: above 118 °C the value of Ptot derates linearly with 7.8 mW/K.

Recommended operating conditions 9

Table 6. Recommended operating conditions

Symbol	Parameter	Conditions		Min	Мах	Unit
V _{CC(A)}	supply voltage A			0.8	3.6	V
V _{CC(B)}	supply voltage B			0.8	3.6	V
VI	input voltage			0	3.6	V
Vo	output voltage	Active mode	[1]	0	V _{cco}	V
		Suspend or 3-state mode		0	3.6	V
T _{amb}	ambient temperature			-40	+125	°C
Δt/ΔV	input transition rise and fall rate	V _{CCI} = 0.8 V to 3.6 V		-	5	ns/V

[1] V_{CCO} is the supply voltage associated with the output port.

10 Static characteristics

Table 7. Typical static characteristics at T_{amb} = 25 °C ^{[1] [2]}

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{OH}	HIGH-level output	V _I = V _{IH} or V _{IL}				
voltage		I _O = -1.5 mA; V _{CC(A)} = V _{CC(B)} = 0.8 V	-	0.69	-	V
V _{OL}	LOW-level output	V _I = V _{IH} or V _{IL}				
	voltage	I_{O} = 1.5 mA; $V_{CC(A)}$ = $V_{CC(B)}$ = 0.8 V	-	0.07	-	V
I _I	input leakage current	DIR input; $V_1 = 0 V \text{ or } 3.6 V$; $V_{CC(A)} = V_{CC(B)} = 0.8 V \text{ to } 3.6 V$	-	±0.025	±0.25	μA
I _{BHL}	bus hold LOW current	$V_{I} = 0.42 \text{ V}; V_{CC(A)} = V_{CC(B)} = 1.2 \text{ V}$	3] _	26	-	μA
I _{BHH}	bus hold HIGH current	$V_{I} = 0.78 \text{ V}; V_{CC(A)} = V_{CC(B)} = 1.2 \text{ V}$	4] _	-24	-	μA
I _{BHLO}	bus hold LOW overdrive current	$V_I = GND$ to V_{CCI} ; $V_{CC(A)} = V_{CC(B)} = 1.2 V$	5] _	28	-	μA
I _{BHHO}	bus hold HIGH overdrive current	$V_I = GND$ to V_{CCI} ; $V_{CC(A)} = V_{CC(B)} = 1.2 V$	6] _	-26	-	μA
I _{OZ}	OFF-state output current	A or B port; $V_0 = 0 V$ or V_{CC0} ; $V_{CC(A)} = V_{CC(B)} = 0.8 V$ to 3.6 V	7] _	±0.5	±2.5	μA
I _{OFF}	power-off leakage current	A port; V ₁ or V _O = 0 V to 3.6 V; V _{CC(A)} = 0 V; V _{CC(B)} = 0.8 V to 3.6 V	-	±0.1	±1	μA
		B port; V ₁ or V _O = 0 V to 3.6 V; V _{CC(B)} = 0 V; V _{CC(A)} = 0.8 V to 3.6 V	-	±0.1	±1	μA
CI	input capacitance	DIR input; $V_1 = 0 V \text{ or } 3.3 V$; $V_{CC(A)} = V_{CC(B)} = 3.3 V$	-	1.0	-	pF
C _{I/O}	input/output capacitance	A and B port; Suspend mode; $V_O = V_{CCO}$ or GND; $V_{CC(A)} = V_{CC(B)} = 3.3 \text{ V}$	-	4.0	-	pF

[1] V_{CCO} is the supply voltage associated with the output port.

[2] V_{CCI} is the supply voltage associated with the data input port. [3] The bus hold circuit can sink at least the minimum low sustaining current at V_{IL} max.

 I_{BHL} should be measured after lowering V_I to GND and then raising it to V_{IL} max. [4] The bus hold circuit can source at least the minimum high sustaining current at V_{IH} min.

 I_{BHH} should be measured after raising V_{I} to V_{CC} and then lowering it to V_{IH} min.

[5] An external driver must source at least I_{BHLO} to switch this node from LOW to HIGH.

[6] An external driver must sink at least I_{BHHO} to switch this node from HIGH to LOW. [7] For I/O ports, the parameter I_{OZ} includes the input leakage current.

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Table 8. Static characteristics ^{[1] [2]}

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	-40 °C te	o +85 °C	-40 °C to	+125 °C	Unit
			Min	Мах	Min	Мах	
V _{IH}	HIGH-level	data input					
	input voltage	V _{CCI} = 0.8 V	0.70V _{CCI}	-	0.70V _{CCI}	-	V
		V _{CCI} = 1.1 V to 1.95 V	0.65V _{CCI}	-	0.65V _{CCI}	-	V
		V _{CCI} = 2.3 V to 2.7 V	1.6	-	1.6	-	V
		V _{CCI} = 3.0 V to 3.6 V	2	-	2	-	V
		DIR input					
		V _{CC(A)} = 0.8 V	0.70V _{CC(A)}	-	0.70V _{CC(A)}	-	V
		V _{CC(A)} = 1.1 V to 1.95 V	0.65V _{CC(A)}	-	0.65V _{CC(A)}	-	V
		V _{CC(A)} = 2.3 V to 2.7 V	1.6	-	1.6	-	V
		V _{CC(A)} = 3.0 V to 3.6 V	2	-	2	-	V
V _{IL}	LOW-level	data input					
	input voltage	V _{CCI} = 0.8 V	-	0.30V _{CCI}	-	0.30V _{CCI}	
		V _{CCI} = 1.1 V to 1.95 V	-	0.35V _{CCI}	-	0.35V _{CCI}	V
		V_{CCI} = 2.3 V to 2.7 V	-	0.7	-	0.7	V
		V _{CCI} = 3.0 V to 3.6 V	-	0.9	-	0.9	V
		DIR input					
		V _{CC(A)} = 0.8 V	-	0.30V _{CC(A)}	-	0.30V _{CC(A)}	V
		V _{CC(A)} = 1.1 V to 1.95 V	-	0.35V _{CC(A)}	-	0.35V _{CC(A)}	V
		V _{CC(A)} = 2.3 V to 2.7 V	-	0.7	-	0.7	V
		V _{CC(A)} = 3.0 V to 3.6 V	-	0.9	-	0.9	V
V _{OH}	HIGH-level	V _I = V _{IH} or V _{IL}					
	output voltage	I_{O} = -100 µA; $V_{CC(A)}$ = $V_{CC(B)}$ = 0.8 V to 3.6 V	V _{CCO} - 0.1	-	V _{CCO} - 0.1	-	V
		I _O = -3 mA; V _{CC(A)} = V _{CC(B)} = 1.1 V	0.85	-	0.85	-	V
		I_{O} = -6 mA; $V_{CC(A)}$ = $V_{CC(B)}$ = 1.4 V	1.05	-	1.05	-	V
		I _O = -8 mA; V _{CC(A)} = V _{CC(B)} = 1.65 V	1.2	-	1.2	-	V
		I_{O} = -9 mA; $V_{CC(A)}$ = $V_{CC(B)}$ = 2.3 V	1.75	-	1.75	-	V
		I _O = -12 mA; V _{CC(A)} = V _{CC(B)} = 3.0 V	2.3	-	2.3	-	V

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Symbol	Parameter	Conditions	-40 °C t	o +85 °C	-40 °C to	+125 °C	Unit
			Min	Max	Min	Max	
V _{OL}	LOW-level	V _I = V _{IH} or V _{IL}					
	output voltage	I_{O} = 100 µA; V _{CC(A)} = V _{CC(B)} = 0.8 V to 3.6 V	-	0.1	-	0.1	V
		I_{O} = 3 mA; $V_{CC(A)}$ = $V_{CC(B)}$ = 1.1 V	-	0.25	-	0.25	V
		$I_{O} = 6 \text{ mA}; V_{CC(A)} = V_{CC(B)} = 1.4 \text{ V}$	-	0.35	-	0.35	V
		I _O = 8 mA; V _{CC(A)} = V _{CC(B)} = 1.65 V	-	0.45	-	0.45	V
		I_{O} = 9 mA; $V_{CC(A)}$ = $V_{CC(B)}$ = 2.3 V	-	0.55	-	0.55	V
		I_{O} = 12 mA; $V_{CC(A)}$ = $V_{CC(B)}$ = 3.0 V	-	0.7	-	0.7	V
I	input leakage current	DIR input; V _I = 0 V or 3.6 V; V _{CC(A)} = V _{CC(B)} = 0.8 V to 3.6 V	-	±1	-	±1.5	μA
I _{BHL}	bus hold LOW	A or B port [3]					
	current	V _I = 0.49 V; V _{CC(A)} = V _{CC(B)} = 1.4 V	15	-	15	-	μA
		V _I = 0.58 V; V _{CC(A)} = V _{CC(B)} = 1.65 V	25	-	25	-	μA
		$V_{I} = 0.70 V; V_{CC(A)} = V_{CC(B)} = 2.3 V$	45	-	45	-	μA
		$V_{I} = 0.80 V; V_{CC(A)} = V_{CC(B)} = 3.0 V$	100	-	90	-	μA
I _{BHH}	bus hold	A or B port ^[4]					
	HIGH current	$V_{I} = 0.91 V; V_{CC(A)} = V_{CC(B)} = 1.4 V$	-15	-	-15	-	μA
		V _I = 1.07 V; V _{CC(A)} = V _{CC(B)} = 1.65 V	-25	-	-25	-	μA
		V_{I} = 1.60 V; $V_{CC(A)}$ = $V_{CC(B)}$ = 2.3 V	-45	-	-45	-	μA
		V_{I} = 2.00 V; $V_{CC(A)}$ = $V_{CC(B)}$ = 3.0 V	-100	-	-100	-	μA
I _{BHLO}	bus hold LOW	A or B port ^[5]					
	overdrive current	$V_{CC(A)} = V_{CC(B)} = 1.6 V$	125	-	125	-	μA
	ourront	$V_{CC(A)} = V_{CC(B)} = 1.95 V$	200	-	200	-	μA
		$V_{CC(A)} = V_{CC(B)} = 2.7 V$	300	-	300	-	μA
		$V_{CC(A)} = V_{CC(B)} = 3.6 V$	500	-	500	-	μA
I _{BHHO}	bus hold	A or B port [6]					
	HIGH overdrive	$V_{CC(A)} = V_{CC(B)} = 1.6 V$	-125	-	-125	-	μA
	current	$V_{CC(A)} = V_{CC(B)} = 1.95 V$	-200	-	-200	-	μA
		$V_{CC(A)} = V_{CC(B)} = 2.7 V$	-300	-	-300	-	μA
		$V_{CC(A)} = V_{CC(B)} = 3.6 V$	-500	-	-500	-	μA
I _{OZ}	OFF-state output current	A or B port; $V_O = 0 V$ or V_{CCO} ; $V_{CC(A)} = V_{CC(B)} = 0.8$ to 3.6 V	-	±5	-	±7.5	μA

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Symbol	Parameter	Conditions	-40 °C t	o +85 °C	-40 °C to	+125 °C	Unit
			Min	Max	Min	Max	
I _{OFF}	power-off leakage	A port; V ₁ or V _O = 0 V to 3.6 V; V _{CC(A)} = 0 V; V _{CC(B)} = 0.8 V to 3.6 V	-	±5	-	±35	μA
	current	B port; V _I or V _O = 0 V to 3.6 V; V _{CC(B)} = 0 V; V _{CC(A)} = 0.8 V to 3.6 V	-	±5	-	±35	μA
I _{CC}	supply current	A port; $V_I = 0 V$ or V_{CCI} ; $I_O = 0 A$					
		$V_{CC(A)} = 0.8 V \text{ to } 3.6 V;$ $V_{CC(B)} = 0.8 V \text{ to } 3.6 V$	-	8	-	11.5	μA
		V _{CC(A)} = 3.6 V; V _{CC(B)} = 0 V	-	8	-	11.5	μA
		V _{CC(A)} = 0 V; V _{CC(B)} = 3.6 V	-2	-	-8	-	μA
		B port; $V_I = 0 V$ or V_{CCI} ; $I_O = 0 A$					
		V _{CC(A)} = 0.8 V to 3.6 V; V _{CC(B)} = 0.8 V to 3.6 V	-	8	-	11.5	μA
		V _{CC(A)} = 3.6 V; V _{CC(B)} = 0 V	-2	-	-8	-	μA
		V _{CC(A)} = 0 V; V _{CC(B)} = 3.6 V	-	8	-	11.5	μA
		A plus B port ($I_{CC(A)} + I_{CC(B)}$); $I_O = 0$ A; $V_I = 0$ V or V_{CCI} ; $V_{CC(A)} = 0.8$ V to 3.6 V; $V_{CC(B)} = 0.8$ V to 3.6 V	-	16	-	23	μA

[1] V_{CCO} is the supply voltage associated with the output port.

[2] V_{CCI} is the supply voltage associated with the data input port. [3] The bus hold circuit can sink at least the minimum low sustaining current at V_{IL} max. I_{BHL} should be measured after lowering VI to GND and then raising it to VIL max.

[4] The bus hold circuit can source at least the minimum high sustaining current at V_{IH} min.

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[6] An external driver must sink at least I_{BHHO} to switch this node from HIGH to LOW. [7] For I/O ports, the parameter I_{OZ} includes the input leakage current.

11 Dynamic characteristics

Table 9. Typical dynamic characteristics at $V_{CC(A)}$ = 0.8 V and T_{amb} = 25 °C ^{[1] [2]}

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 7; for wave forms see Figure 5 and Figure 6

Symbol	Parameter	Conditions			Vco	С(В)			Unit
			0.8 V	1.2 V	1.5 V	1.8 V	2.5 V	3.3 V	
t _{pd}	propagation delay	A to B	15.8	8.4	8.0	8.0	8.7	9.5	ns
		B to A	15.8	12.7	12.4	12.2	12.0	11.8	ns
t _{dis}	disable time	DIR to A	12.2	12.2	12.2	12.2	12.2	12.2	ns
		DIR to B	11.7	7.9	7.6	8.2	8.7	10.2	ns
t _{en}	enable time	DIR to A	27.5	20.6	20.0	20.4	20.7	22.0	ns
		DIR to B	28.0	20.6	20.2	20.2	20.9	21.7	ns

[1] t_{pd} is the same as t_{PLH} and t_{PHL} ; t_{dis} is the same as t_{PLZ} and t_{PHZ} ; t_{en} is the same as t_{PZL} and t_{PZH} .

[2] t_{en} is a calculated value using the formula shown in <u>Section 12.4</u>

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Symbol	Parameter	Conditions			Vc	C(A)			Unit
			0.8 V	1.2 V	1.5 V	1.8 V	2.5 V	3.3 V	
t _{pd}	propagation delay	A to B	15.8	12.7	12.4	12.2	12.0	11.8	ns
		B to A	15.8	8.4	8.0	8.0	8.7	9.5	ns
t _{dis}	disable time	DIR to A	12.2	4.9	3.8	3.7	2.8	3.4	ns
		DIR to B	11.7	9.2	9.0	8.8	8.7	8.6	ns
t _{en}	enable time	DIR to A	27.5	17.6	17.0	16.8	17.4	18.1	ns
		DIR to B	28.0	17.6	16.2	15.9	14.8	15.2	ns

Table 10. Typical dynamic characteristics at V_{CC(B)} = 0.8 V and T_{amb} = 25 °C $^{[1]}$ $^{[2]}$ Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 7; for wave forms see Figure 5 and Figure 6

 $[1] t_{pd} is the same as t_{PLH} and t_{PHL}; t_{dis} is the same as t_{PLZ} and t_{PHZ}; t_{en} is the same as t_{PZL} and t_{PZH}. \\ [2] t_{en} is a calculated value using the formula shown in <u>Section 12.4</u>$

Table 11. Typical power dissipation capacitance at $V_{CC(A)} = V_{CC(B)}$ and $T_{amb} = 25 \ ^{\circ}C^{[1][2]}$

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	$V_{CC(A)}$ and $V_{CC(B)}$						
			0.8 V	1.2 V	1.5 V	1.8 V	2.5 V	3.3 V	
C _{PD}	power dissipation capacitance	A port: (direction A to B); B port: (direction B to A)	1	2	2	2	2	2	pF
		A port: (direction B to A); B port: (direction A to B)	9	11	11	12	14	17	pF

[1] C_{PD} is used to determine the dynamic power dissipation (P_D in μ W).

 $P_{D} = C_{PD} \times V_{CC}^{2} \times f_{i} \times N + \Sigma (C_{L} \times V_{CC}^{2} \times f_{o}) \text{ where:}$

 f_i = input frequency in MHz;

f_o = output frequency in MHz;

 C_L = load capacitance in pF;

V_{CC} = supply voltage in V;

N = number of inputs switching;

$$\begin{split} &\Sigma(C_L \times V_{CC}^2 \times f_o) = \text{sum of the outputs.} \\ &[2] \quad f_i = 10 \text{ MHz; } V_I = \text{GND to } V_{CC}; \ t_r = t_f = 1 \text{ ns; } C_L = 0 \text{ pF; } R_L = \infty \Omega. \end{split}$$

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Symbol	Parameter	Conditions					Vc	C(B)					Unit
			1.2 V :	±0.1 V	1.5 V	±0.1 V	1.8 V ±	±0.15 V	2.5 V	±0.2 V	3.3 V	±0.3 V	
			Min	Max	Min	Мах	Min	Max	Min	Max	Min	Мах	_
V _{CC(A)} =	1.1 V to 1.3 V				1					,			
t _{pd}	propagation	A to B	1.0	9.0	0.7	6.8	0.6	6.1	0.5	5.7	0.5	6.1	ns
	delay	B to A	1.0	9.0	0.8	8.0	0.7	7.7	0.6	7.2	0.5	7.1	ns
t _{dis}	disable time	DIR to A	2.2	8.8	2.2	8.8	2.2	8.8	2.2	8.8	2.2	8.8	ns
		DIR to B	2.2	8.4	1.8	6.7	2.0	6.9	1.7	6.2	2.4	7.2	ns
t _{en}	enable time	DIR to A	-	17.4	-	14.7	-	14.6	-	13.4	-	14.3	ns
		DIR to B	-	17.8	-	15.6	-	14.9	-	14.5	-	14.9	ns
V _{CC(A)} =	1.4 V to 1.6 V									,			
t _{pd}	propagation	A to B	1.0	8.0	0.7	5.4	0.6	4.6	0.5	3.7	0.5	3.5	ns
	delay	B to A	1.0	6.8	0.8	5.4	0.7	5.1	0.6	4.7	0.5	4.5	ns
t _{dis}	disable time	DIR to A	1.6	6.3	1.6	6.3	1.6	6.3	1.6	6.3	1.6	6.3	ns
		DIR to B	2.0	7.6	1.8	5.9	1.6	6.0	1.2	4.8	1.7	5.5	ns
t _{en}	enable time	DIR to A	-	14.4	-	11.3	-	11.1	-	9.5	-	10.0	ns
		DIR to B	-	14.3	-	11.7	-	10.9	-	10.0	-	9.8	ns
V _{CC(A)} =	1.65 V to 1.95	V	.1	1	1	1	1	1		1	1	1	
t _{pd}	propagation	A to B	1.0	7.7	0.6	5.1	0.5	4.3	0.5	3.4	0.5	3.1	ns
	delay	B to A	1.0	6.1	0.7	4.6	0.5	4.4	0.5	3.9	0.5	3.7	ns
t _{dis}	disable time	DIR to A	1.6	5.5	1.6	5.5	1.6	5.5	1.6	5.5	1.6	5.5	ns
		DIR to B	1.8	7.8	1.8	5.7	1.4	5.8	1.0	4.5	1.5	5.2	ns
t _{en}	enable time	DIR to A	-	13.9	-	10.3	-	10.2	-	8.4	-	8.9	ns
		DIR to B	-	13.2	-	10.6	-	9.8	-	8.9	-	8.6	ns
$V_{CC(A)} = 2$	2.3 V to 2.7 V		1	1	1	1	1	1		1	1	1	
t _{pd}	propagation	A to B	1.0	7.2	0.5	4.7	0.5	3.9	0.5	3.0	0.5	2.6	ns
	delay	B to A	1.0	5.7	0.6	3.8	0.5	3.4	0.5	3.0	0.5	2.8	ns
t _{dis}	disable time	DIR to A	1.5	4.2	1.5	4.2	1.5	4.2	1.5	4.2	1.5	4.2	ns
		DIR to B	1.7	7.3	2.0	5.2	1.5	5.1	0.6	4.2	1.1	4.8	ns
t _{en}	enable time	DIR to A	-	13.0	-	9.0	-	8.5	-	7.2	-	7.6	ns
		DIR to B	_	11.4	_	8.9	_	8.1	_	7.2	_	6.8	ns

Table 12. Dynamic characteristics for temperature range -40 °C to +85 °C ^{[1] [2]} Voltages are referenced to GND (ground = 0.V): for test circuit see Figure 7: for wave forms see Figure 5 and Figure 6.

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Dual-bit, dual-supply voltage level translator/transceiver; 3-state

Symbol	Parameter	Conditions	_	V _{CC(B)}									
			1.2 V	.2 V ±0.1 V 1.5 V ±0.1 V 1		1.8 V ±0.15 V		2.5 V ±0.2 V		3.3 V ±0.3 V			
			Min	Max	Min	Мах	Min	Мах	Min	Мах	Min	Мах	
V _{CC(A)} = :	3.0 V to 3.6 V			-		1	1	1	1		1	1	
t _{pd} propagation	A to B	1.0	7.1	0.5	4.5	0.5	3.7	0.5	2.8	0.5	2.4	ns	
	delay	B to A	1.0	6.1	0.6	3.6	0.5	3.1	0.5	2.6	0.5	2.4	ns
t _{dis}	disable time	DIR to A	1.5	4.7	1.5	4.7	1.5	4.7	1.5	4.7	1.5	4.7	ns
		DIR to B	1.7	7.2	0.7	5.5	0.6	5.5	0.7	4.1	1.7	4.7	ns
t _{en}	enable time	DIR to A	-	13.3	-	9.1	-	8.6	-	6.7	-	7.1	ns
		DIR to B	-	11.8	-	9.2	-	8.4	-	7.5	-	7.1	ns

Table 13. Dynamic characteristics for temperature range -40 °C to +125 °C ^{[1] [2]}

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 7; for wave forms see Figure 5 and Figure 6

Symbol	Parameter	Conditions					Vc	C(B)					Unit
			1.2 V	±0.1 V	1.5 V	±0.1 V	1.8 V ±	±0.15 V	2.5 V	±0.2 V	3.3 V	±0.3 V]
			Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
V _{CC(A)} =	1.1 V to 1.3 V			1		1	1	1	1	1	1	1	
t _{pd}	propagation	A to B	1.0	9.9	0.7	7.5	0.6	6.8	0.5	6.3	0.5	6.8	ns
	delay	B to A	1.0	9.9	0.8	8.8	0.7	8.5	0.6	8.0	0.5	7.9	ns
t _{dis}	disable time	DIR to A	2.2	9.7	2.2	9.7	2.2	9.7	2.2	9.7	2.2	9.7	ns
		DIR to B	2.2	9.2	1.8	7.4	2.0	7.6	1.7	6.9	2.4	8.0	ns
t _{en}	enable time	DIR to A	-	19.1	-	16.2	-	16.1	-	14.9	-	15.9	ns
		DIR to B	-	19.6	-	17.2	-	16.5	-	16.0	-	16.5	ns
V _{CC(A)} =	1.4 V to 1.6 V												
t _{pd}	propagation	A to B	1.0	8.8	0.7	6.0	0.6	5.1	0.5	4.1	0.5	3.9	ns
	delay	B to A	1.0	7.5	0.8	6.0	0.7	5.7	0.6	5.2	0.5	5.0	ns
t _{dis}	disable time	DIR to A	1.6	7.0	1.6	7.0	1.6	7.0	1.6	7.0	1.6	7.0	ns
		DIR to B	2.0	8.3	1.8	6.5	1.6	6.6	1.2	5.3	1.7	6.1	ns
t _{en}	enable time	DIR to A	-	15.8	-	12.5	-	12.3	-	10.5	-	11.1	ns
		DIR to B	-	15.8	-	13.0	-	12.7	-	11.1	-	10.9	ns
V _{CC(A)} =	1.65 V to 1.95	V			,								_
t _{pd}	propagation	A to B	1.0	8.5	0.6	5.7	0.5	4.8	0.5	3.8	0.5	3.5	ns
	delay	B to A	1.0	6.8	0.7	5.1	0.5	4.9	0.5	4.3	0.5	4.1	ns
t _{dis}	disable time	DIR to A	1.6	6.1	1.6	6.1	1.6	6.1	1.6	6.1	1.6	6.1	ns
		DIR to B	1.8	8.6	1.8	6.3	1.4	6.4	1.0	5.0	1.5	5.8	ns
t _{en}	enable time	DIR to A	-	15.4	-	11.4	-	11.3	-	9.3	-	9.9	ns
		DIR to B	_	14.6	-	11.8	-	10.9	-	9.9	-	9.6	ns

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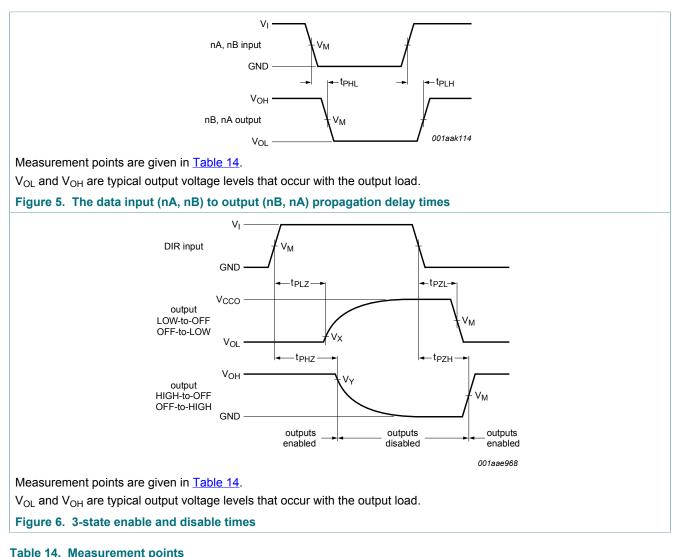
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Dual-bit, dual-supply voltage level translator/transceiver; 3-state

Symbol	Parameter	Conditions					Vc	C(B)					Unit
			1.2 V	±0.1 V	1.5 V	±0.1 V	1.8 V ±	:0.15 V	2.5 V	±0.2 V	3.3 V	±0.3 V	
			Min	Мах	Min	Max	Min	Мах	Min	Max	Min	Max	
$V_{CC(A)} =$	2.3 V to 2.7 V					1			1			1	
t _{pd}	propagation	A to B	1.0	8.0	0.5	5.2	0.5	4.3	0.5	3.3	0.5	2.9	ns
	delay	B to A	1.0	6.3	0.6	4.2	0.5	3.8	0.5	3.3	0.5	3.1	ns
t _{dis}	disable time	DIR to A	1.5	4.7	1.5	4.7	1.5	4.7	1.5	4.7	1.5	4.7	ns
		DIR to B	1.7	8.0	2.0	5.8	1.5	5.7	0.6	4.7	1.1	5.3	ns
t _{en}	enable time	DIR to A	-	14.3	-	10.0	-	9.5	-	8.0	-	8.4	ns
		DIR to B	-	12.7	-	9.9	-	9.0	-	8.0	-	7.6	ns
V _{CC(A)} =	3.0 V to 3.6 V												
t _{pd}	propagation	A to B	1.0	7.9	0.5	5.0	0.5	4.1	0.5	3.1	0.5	2.7	ns
	delay	B to A	1.0	6.8	0.6	4.0	0.5	3.5	0.5	2.9	0.5	2.7	ns
t _{dis}	disable time	DIR to A	1.5	5.2	1.5	5.2	1.5	5.2	1.5	5.2	1.5	5.2	ns
		DIR to B	1.7	7.9	0.7	6.1	0.6	6.1	0.7	4.6	1.7	5.2	ns
t _{en}	enable time	DIR to A	-	14.7	-	10.1	-	9.6	-	7.5	-	7.9	ns
		DIR to B	-	13.1	-	10.2	-	9.3	-	8.3	-	7.9	ns

Dual-bit, dual-supply voltage level translator/transceiver; 3-state

11.1 Waveforms and test circuit



Supply voltage	Input ^[1]	Output ^[2]		
V _{CC(A)} , V _{CC(B)}	V _M	V _M	V _X	V _Y
1.1 V to 1.6 V	0.5V _{CCI}	0.5V _{CCO}	V _{OL} + 0.1 V	V _{OH} - 0.1 V
1.65 V to 2.7 V	0.5V _{CCI}	0.5V _{CCO}	V _{OL} + 0.15 V	V _{OH} - 0.15 V
3.0 V to 3.6 V	0.5V _{CCI}	0.5V _{CCO}	V _{OL} + 0.3 V	V _{OH} - 0.3 V

[1] V_{CCI} is the supply voltage associated with the data input port.

[2] V_{CCO} is the supply voltage associated with the output port.

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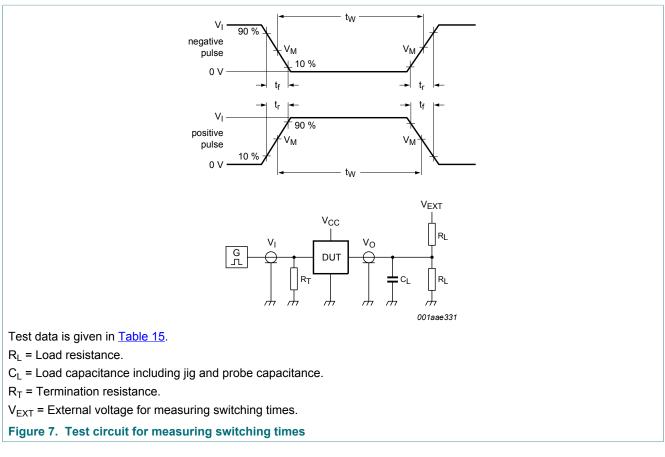


Table 15. Test data

Supply voltage	Input	•		Load		V _{EXT}		
$V_{CC(A)}, V_{CC(B)}$	V _I ^[1]	Δt/ΔV ^[2]	CL	RL	t _{PLH} , t _{PHL}	t _{PZH} , t _{PHZ}	t _{PZL} , t _{PLZ} ^[3]	
1.1 V to 1.6 V	V _{CCI}	≤ 1.0 ns/V	15 pF	2 kΩ	open	GND	2V _{CCO}	
1.65 V to 2.7 V	V _{CCI}	≤ 1.0 ns/V	15 pF	2 kΩ	open	GND	2V _{CCO}	
3.0 V to 3.6 V	V _{CCI}	≤ 1.0 ns/V	15 pF	2 kΩ	open	GND	2V _{CCO}	

12 Application information

12.1 Unidirectional logic level-shifting application

The circuit given in Figure 8 is an example of the 74AVCH2T45 being used in an unidirectional logic level-shifting application.

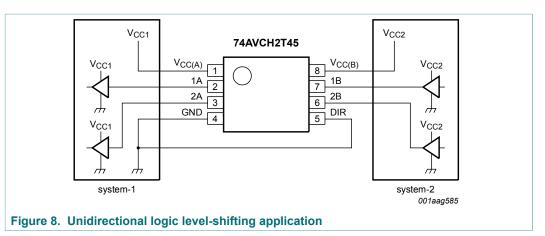


Table 16. Unidirectional logic level-shifting application

Pin	Name	Function	Description
1	V _{CC(A)}	V _{CC1}	supply voltage of system-1 (0.8 V to 3.6 V)
2	1A	OUT1	output level depends on V _{CC1} voltage
3	2A	OUT2	output level depends on V _{CC1} voltage
4	GND	GND	device GND
5	DIR	DIR	the GND (LOW level) determines B port to A port direction
6	2B	IN2	input threshold value depends on V_{CC2} voltage
7	1B	IN1	input threshold value depends on V_{CC2} voltage
8	V _{CC(B)}	V _{CC2}	supply voltage of system-2 (0.8 V to 3.6 V)

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12.2 Bidirectional logic level-shifting application

Figure 9 shows the 74AVCH2T45 being used in a bidirectional logic level-shifting application. Since the device does not have an output enable (OE) pin, the system designer should take precautions to avoid bus contention between system-1 and system-2 when changing directions.

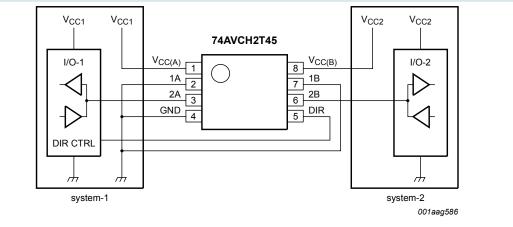


Figure 9. Bidirectional logic level-shifting application

<u>Table 17</u> gives a sequence that will illustrate data transmission from system-1 to system-2 and then from system-2 to system-1.

Table 17.	Bidirectional logic	level-shifting	application ^[1]
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State	DIR CTRL	I/O-1	I/O-2	Description
1	Н	output	input	system-1 data to system-2
2	Η	Z	Z	system-2 is getting ready to send data to system-1. I/O-1 and I/O-2 are disabled. The bus-line state depends on bus hold.
3	L	Z	Z	DIR bit is set LOW. I/O-1 and I/O-2 still are disabled. The bus-line state depends on bus hold.
4	L	input	output	system-2 data to system-1

[1] H = HIGH voltage level;

L = LOW voltage level;

Z = high-impedance OFF-state.

12.3 Power-up considerations

The device is designed such that no special power-up sequence is required other than GND being applied first.

V _{CC(A)}	V _{CC(B)}							Unit
	0 V	0.8 V	1.2 V	1.5 V	1.8 V	2.5 V	3.3 V	
0 V	0	0.1	0.1	0.1	0.1	0.1	0.1	μA
0.8 V	0.1	0.1	0.1	0.1	0.1	0.7	2.3	μA
1.2 V	0.1	0.1	0.1	0.1	0.1	0.3	1.4	μA
1.5 V	0.1	0.1	0.1	0.1	0.1	0.1	0.9	μA
1.8 V	0.1	0.1	0.1	0.1	0.1	0.1	0.5	μA
2.5 V	0.1	0.7	0.3	0.1	0.1	0.1	0.1	μA
3.3 V	0.1	2.3	1.4	0.9	0.5	0.1	0.1	μA

Table 18. Typicaltotal supply current (I_{CC(A)} + I_{CC(B)})

12.4 Enable times

The enable times for the 74AVCH2T45 are calculated from the following formulas:

- t_{en} (DIR to nA) = t_{dis} (DIR to nB) + t_{pd} (nB to nA)
- t_{en} (DIR to nB) = t_{dis} (DIR to nA) + t_{pd} (nA to nB)

In a bidirectional application, these enable times provide the maximum delay from the time the DIR bit is switched until an output is expected. For example, if the 74AVCH2T45 initially is transmitting from A to B, then the DIR bit is switched, the B port of the device must be disabled before presenting it with an input. After the B port has been disabled, an input signal applied to it appears on the corresponding A port after the specified propagation delay.

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13 Package outline

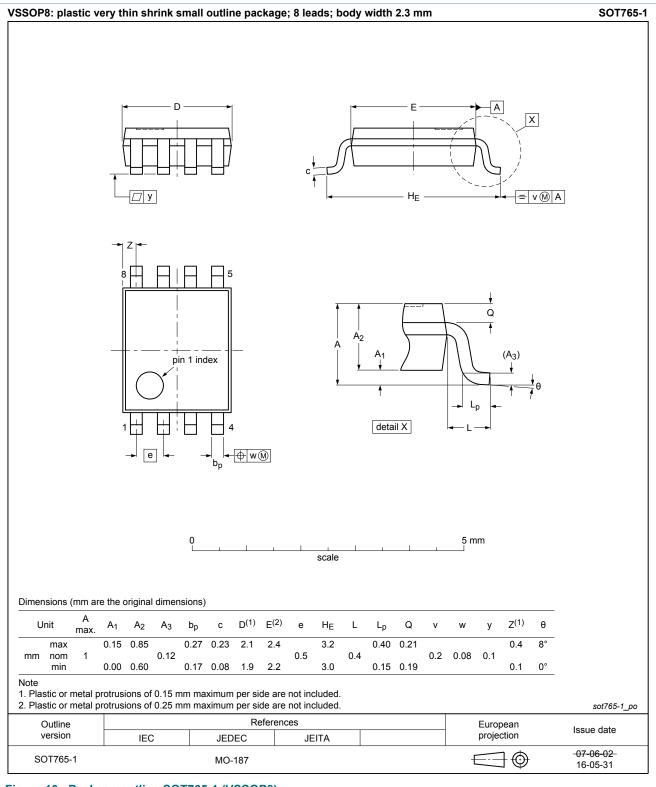


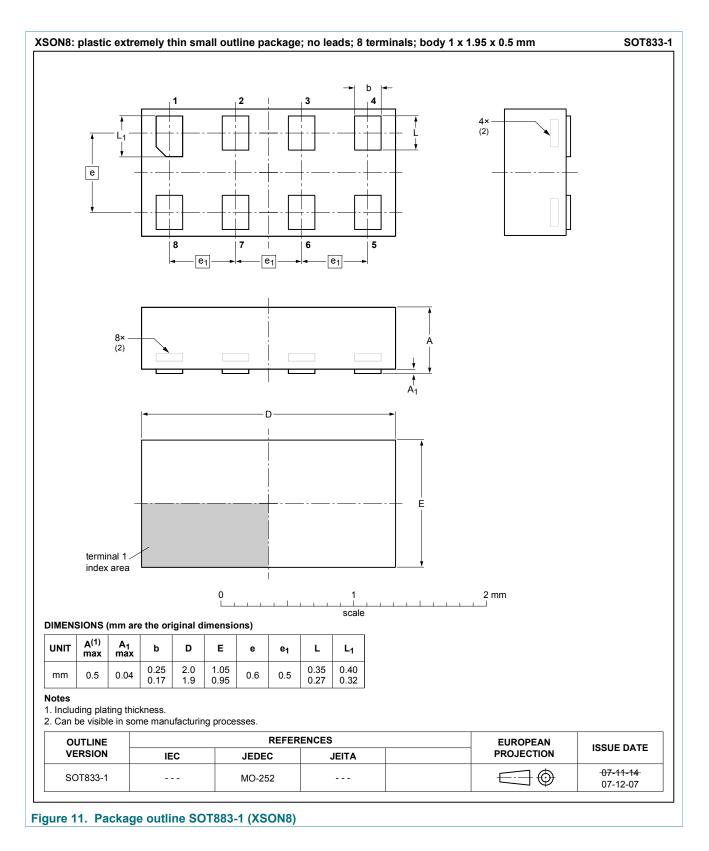
Figure 10. Package outline SOT765-1 (VSSOP8)

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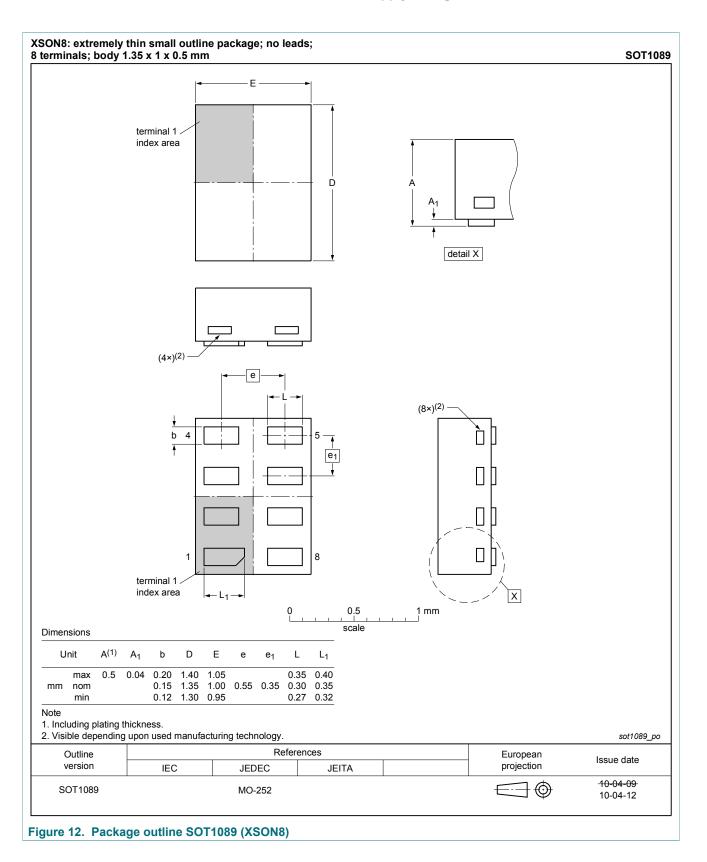
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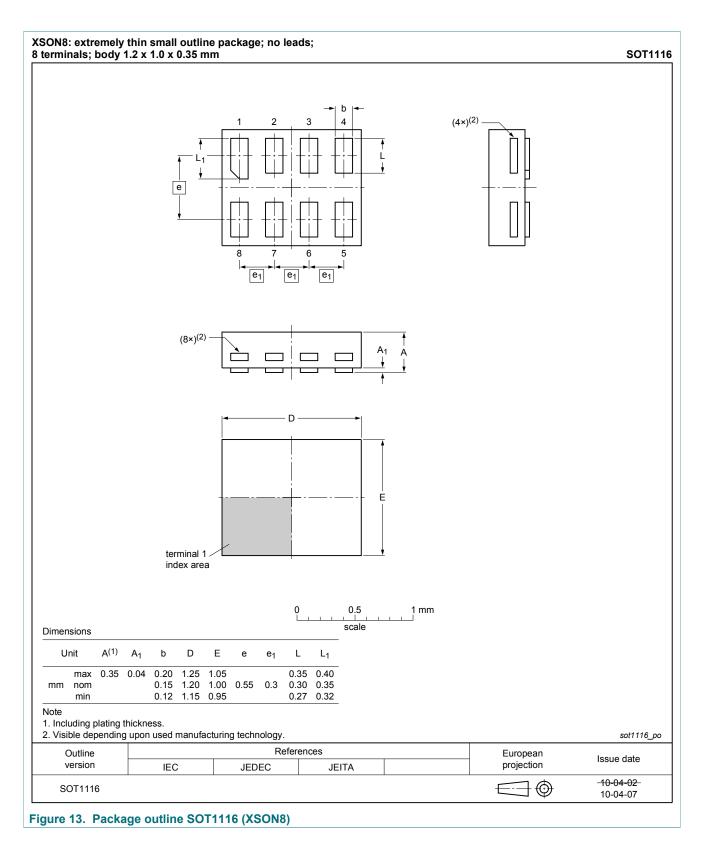


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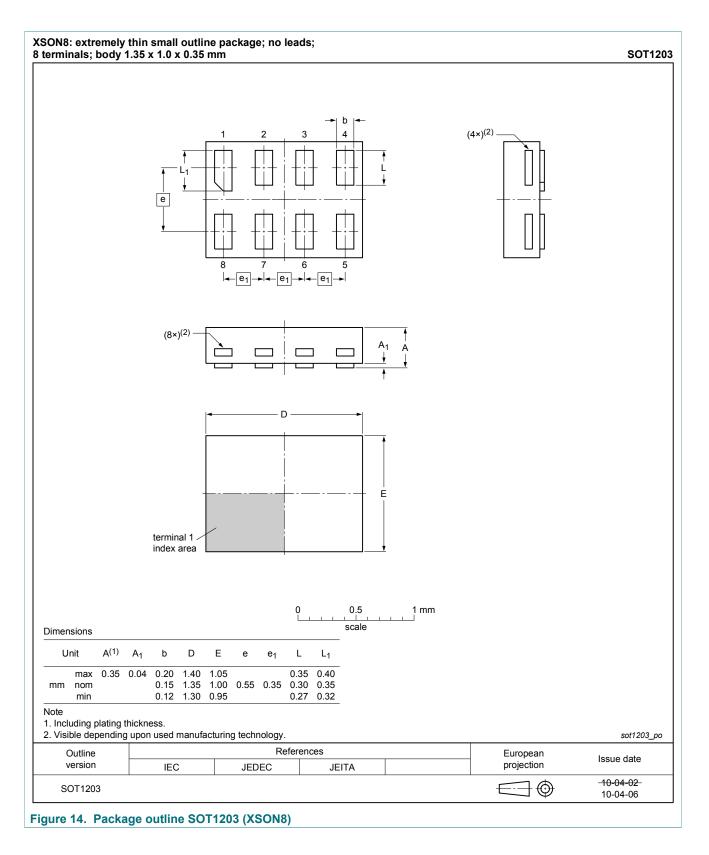


74AVCH2T45 Product data sheet

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Dual-bit, dual-supply voltage level translator/transceiver; 3-state



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Product data sheet

14 Abbreviations

Table 19. Abbreviations	
Acronym	Description
CDM	Charged Device Model
DUT	Device Under Test
ESD	ElectroStatic Discharge
НВМ	Human Body Model
ММ	Machine Model

15 Revision history

Table 20. Revision hi	istory					
Document ID	Release date	Data sheet status	Change notice	Supersedes		
74AVCH2T45 v.7	20180220	Product data sheet	-	74AVCH2T45 v.6		
Modifications:	Nexperia. Legal texts have 	 The format of this data sheet has been redesigned to comply with the identity guidelines of Nexperia. Legal texts have been adapted to the new company name where appropriate. Removed type number 74AVCH2T45GD (SOT996-2/XSON8) 				
74AVCH2T45 v.6	20130402	Product data sheet	-	74AVCH2T45 v.5		
Modifications:	For type numb	For type number 74AVCH2T45GD XSON8U has changed to XSON8.				
74AVCH2T45 v.5	20111214	Product data sheet	-	74AVCH2T45 v.4		
Modifications:	Legal pages updated.					
74AVCH2T45 v.4	20101124	Product data sheet	-	74AVCH2T45 v.3		
74AVCH2T45 v.3	20090506	Product data sheet	-	74AVCH2T45 v.2		
74AVCH2T45 v.2	20090203	Product data sheet	-	74AVCH2T45 v.1		
74AVCH2T45 v.1	20070703	Product data sheet	-	-		

16 Legal information

16.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

Please consult the most recently issued document before initiating or completing a design. [1]

The term 'short data sheet' is explained in section "Definitions".

[2] [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nexperia.com.

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Dual-bit, dual-supply voltage level translator/transceiver; 3-state

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Dual-bit, dual-supply voltage level translator/transceiver; 3-state

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